

Performance

- Technology: 0.5um Power HEMT
- Frequency: 0.135~0.275GHz
- Typical Pout: 58dBm
- Typical Gain: 16dB
- Typical PAE: 70%
- Bias: 42V/-3.1V
- Package: Metal Ceramic

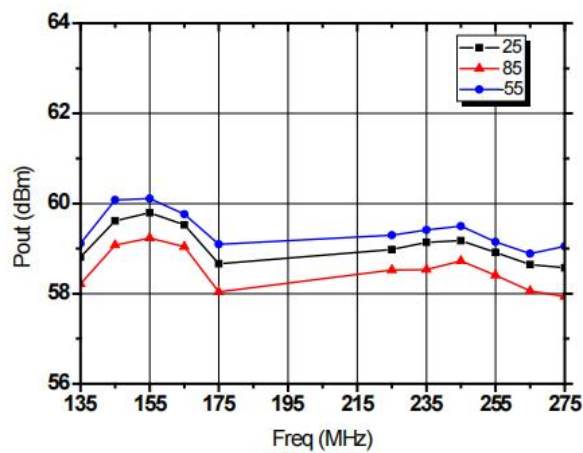


Electrical Specifications ($T_A=25^{\circ}\text{C}$, $V_d=42\text{V}$ (PL=1ms, D.C=25%), $V_g=-3.1\text{V}$, F: 0.135~0.275GHz)

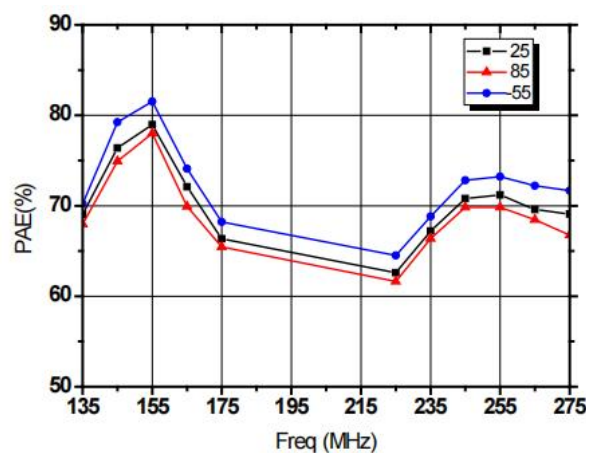
Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	-	58	-	dBm
Gp	Power Gain	-	16	-	dB
η_{add}	Power Added Efficiency	-	70	-	%
ΔG_p	Gain Flatness	-0.5	-	+0.5	dB

Test Curves

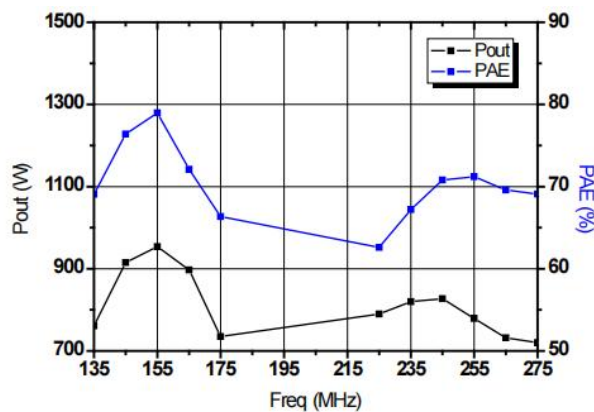
Pout&Freq. @ Different Temp.



PAE&Freq. @ Different Temp.



Pout、PAE&Freq.

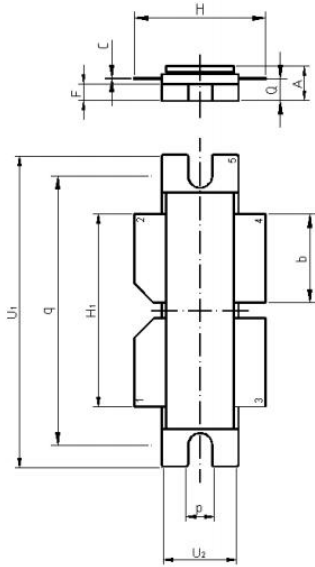


Absolute Max Ratings (TA=25°C)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	50V	
Vg	Grid Voltage	-10~+2V	
Tch	Channel Temperature	225°C	【1】
Tstg	Storage Temperature	-55~175°C	
Tc	Operating Temperature	-45~85°C	

【1】 Exceeding any one or combination of these limits may cause permanent damage.

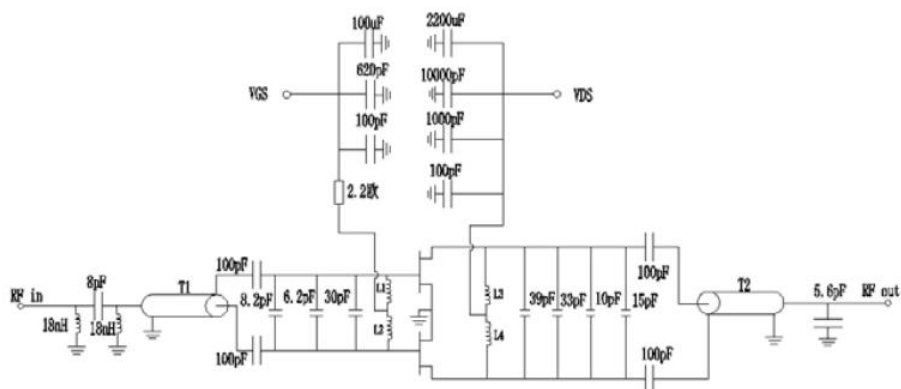
Outline Drawing



Dimension symbols

Symbol	Value (unit: mm)	
	Min.	Max.
A	3.4	5.0
b	8.27	8.53
C	0.10	0.15
F	1.57	2.47
H	15.6	16.29
H1	18.57	18.83
P	3.13	3.39
Q	2.08	3.02
q	27.81	28.07
U1	33.91	34.17
U2	10.03	10.29

Application Circuit



Note:

- (1) Connect the circuit according to the diagram, pay attention to anti-static, and ensure good grounding and heat dissipation when using power devices;
- (2) In order to ensure the good performance of the power module, the capacity value of the power filter and the energy storage capacitor shall be reasonably selected according to the modulation mode during pulse operation;
- (3) Power module power-up sequence VGS, VDS;
- (4) Power module power-off sequence VDS, VGS.